TOSHIBA {DISCRETE/OPTO}

56 DE 9097250 0007606 2

9097250 TOSHIBA (DISCRETE/OPTO)

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

56C 07606 D T-33-07 2SC2824

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

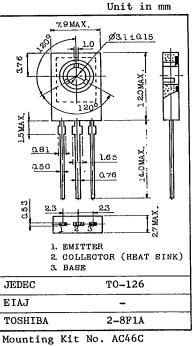
FEATURES:

- Complementary to 2SA1184.
- Suitable for driver of 60 to 80 watts audio amplifier,
- · High breakdown voltage.

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MAXIMUM RATINGS (Ta	=25°C)				
CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		VCBO	120	v	
Collector-Emitter Voltage		V _{CEO} 120		v	
Emitter-Base Voltage		VEBO	5	v	
Collector Current		IC	1	A	
Base Current		ГB	100	mA	
Collector Power Dissipation	Ta=25°C	PC	1	W][]
	Tc=25°C		15		Ľ
Junction Temperature		Тј	150	°C	1
Storage Temperature Range		Tstg	stg -55~150] `



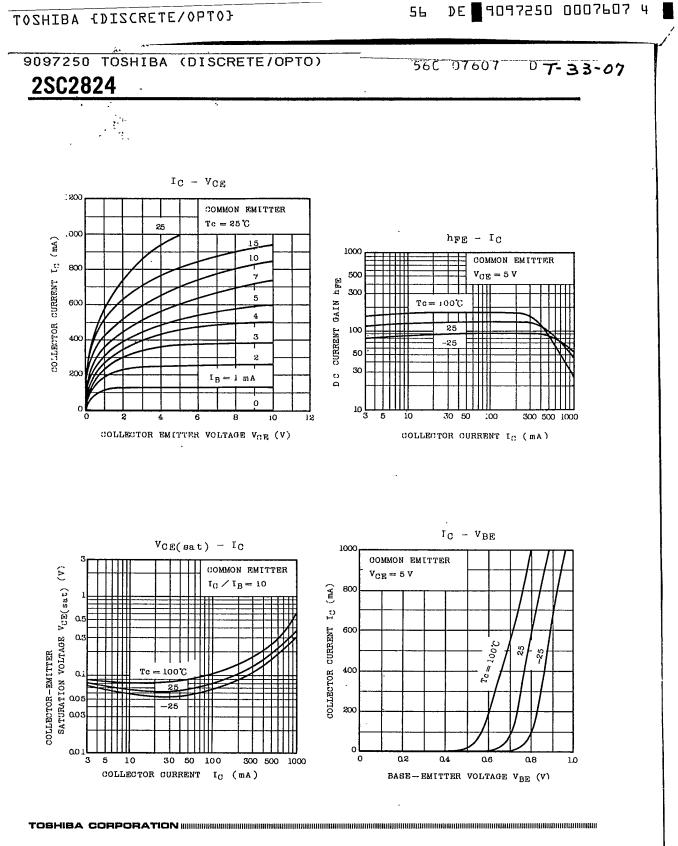
Weight : 0.72g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} =120V,	I _E =0	-	-	100	nA
Emitter Cut-off Current	IEBO	$V_{\rm EB}=5V$,	I _C =0	-	-	100	nA
Collector-Emitter Breakdown Voltage	V(BR)CEO	IC=10mA,	IB=0	120	-	-	v
Emitter-Base Breakdown Voltage	V(BR)EBO	$I_E = lmA$,	I _C =0	5	-	-	v
DC Current Gain	h _{FE} (Note)	V _{CE} =5V,	I _C =100mA	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE}(sat)$	I _C =50OmA,	IB=50mA	-	0.30	1.0	v
Base-Emitter Voltage	VBE	$V_{CE}=5V$,	IC=500mA	-	0.78	1.0	v
Transition Frequency	fT	V _{CE} =5V,	IC=100mA	-	120	-	MHz
Collector Output Capacitance	Cob	V _{CB} =10V,	$I_E=0$, f=1MHz	-	15	-	pF

Note: hFE Classification

0:80~160 Y:120~240



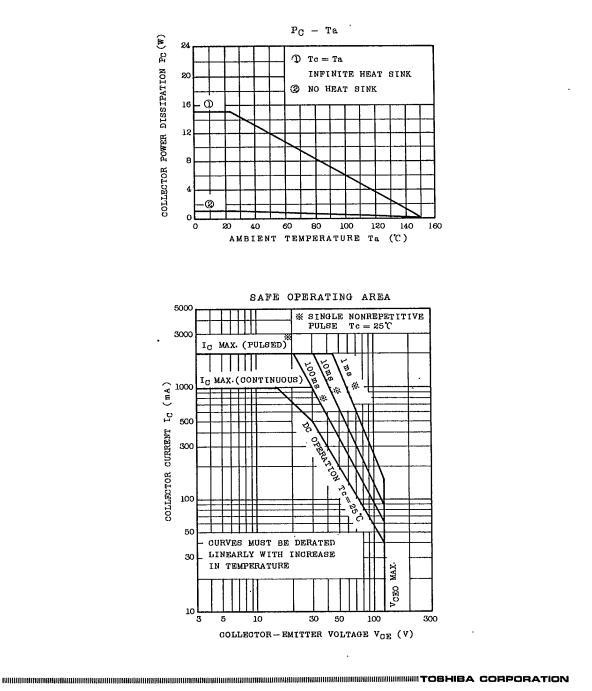


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DT-33-07 2SC2824



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